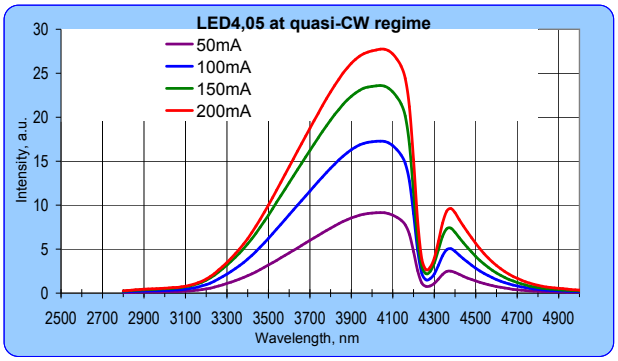
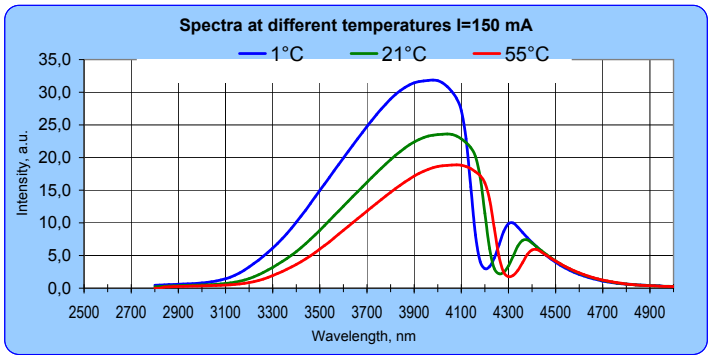
Mid-Infrared Light Emitting Diode 4,05 μm

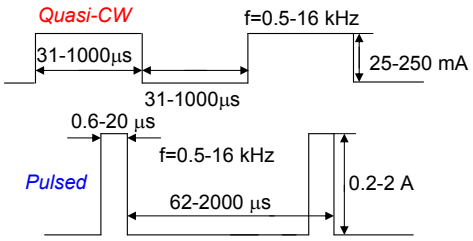
Light Emitting Diodes with central wavelength 4,1 μm series are based on heterostructures grown on InAs substrates by MOCVD. InAsSb is used in the active layer. Wide band gap solid solutions InAsSbP with P content 50% are used for good electron confinement.

Parameters	Units	Conditions	Ratings		
			Min	Typ	Max
Peak emission wavelength	μm	T=300 K	3,95	4,05	4,10
FWHM of the emission band	nm	150 mA CW	700	850	1000
Quasi-CW Optical Power	μW	200 mA qCW	15	20	30
Pulsed Optical Power	μW	1 A	180	200	220
Switching Time	ns	T=300 K	10	20	30
Operating Temperature Range, °C	-240° ÷ +50°				
Emitting Area, μm	300x300				
Soldering temperature	260 °C				

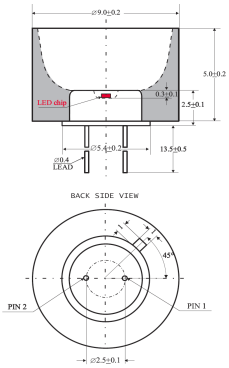
Package	
TO-18 with a non-removable cap without a window	MID IR LED
TO-18 with a parabolic reflector without a window	**MID IR LED-PR**
TO-18 with a parabolic reflector with a window	MID IR LED-PRwin
TO-5 with a built-in thermocooler and thermoresistor, covered by a cap with a window	MID IR LED-TEC
TO-5 with a built-in thermocooler and thermoresistor, covered by a parabolic reflector with a window	MID IR LED-TEC-PR

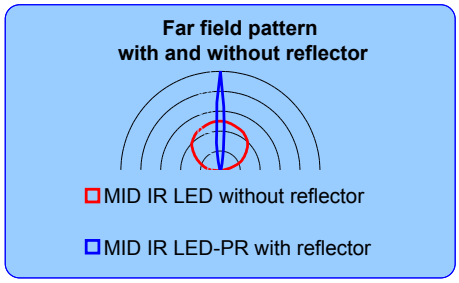


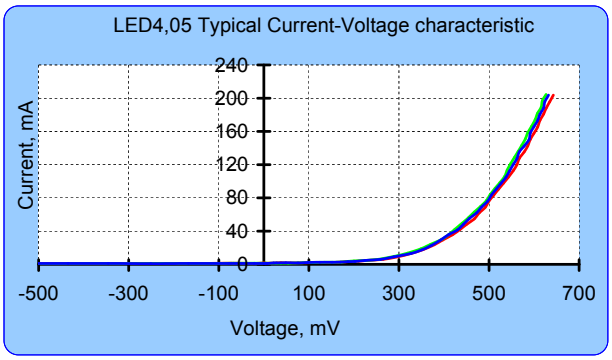


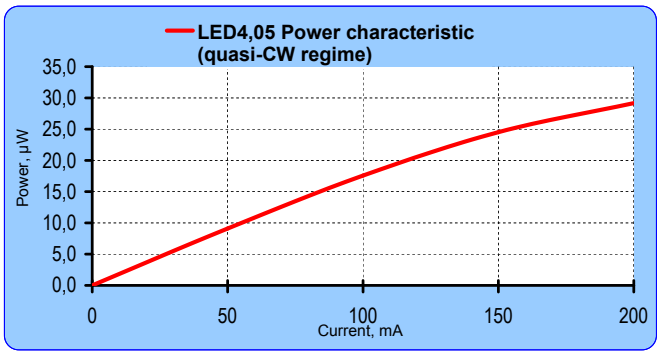


Maximum current is 220 mA at quasi-CW
Maximum pulsed current is 1 A (duration 500 ns, repetition rate 2 kHz)
Optimal operating current is 150-200 mA at quasi-CW.









RELATED PRODUCTS

LED driver D-31M can be used for LED power supply in quasi-CW and pulse modes
LED driver mD-1c can be used for LED power supply in a quasi-CW mode
LED driver mD-1p can be used for LED power supply in a pulse mode

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